

# HSB88AS

Silicon Schottky Barrier Diode for High Speed Switching

# HITACHI

ADE-208-964 (Z)

Rev. 0  
Aug. 2000

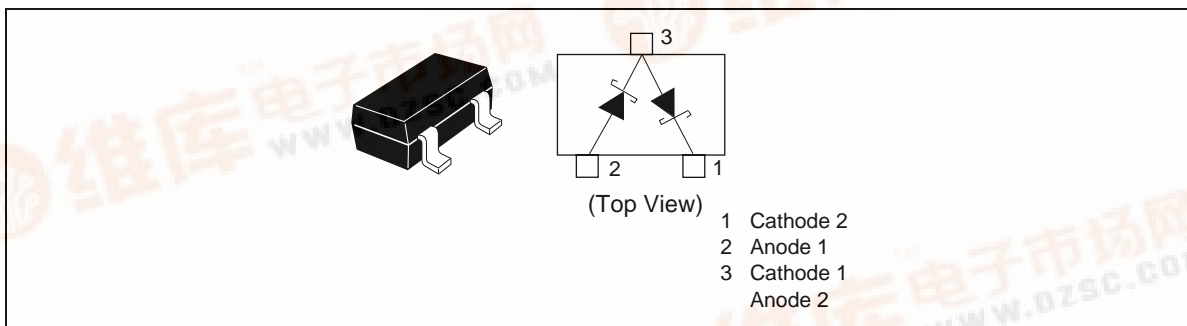
## Features

- Low reverse current, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

## Ordering Information

Type No.	Laser Mark	Package Code
HSB88AS	C1	CMPAK

## Pin Arrangement



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## HSB88AS

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### Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	$V_R$	10	V
Average rectified current	$I_o^*$	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: Per one device.

### Electrical Characteristics \*<sup>1</sup>

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	0.350	—	0.420	V	$I_F = 1 \text{ mA}$
	$V_{F2}$	0.500	—	0.580		$I_F = 10 \text{ mA}$
Reverse current	$I_{R1}$	—	—	0.2	$\mu\text{A}$	$V_R = 2 \text{ V}$
	$I_{R2}$	—	—	10		$V_R = 10 \text{ V}$
Capacitance	C	—	—	0.80	pF	$V_R = 0 \text{ V}$ , f = 1 MHz
Capacitance deviation	$\Delta C$	—	—	0.10	pF	$V_R = 0 \text{ V}$ , f = 1 MHz
Forward voltage deviation	$\Delta V_F$	—	—	10	mV	$I_F = 10 \text{ mA}$
ESD-Capability <sup>2</sup>	—	30	—	—	V	C = 200 pF, R = 0 $\Omega$ , Both forward and reverse direction 1 pulse.

Notes: 1. Per one device.

2. Failure criterion ;  $I_R > 0.4 \mu\text{A}$  at  $V_R = 2\text{V}$

Main Characteristic

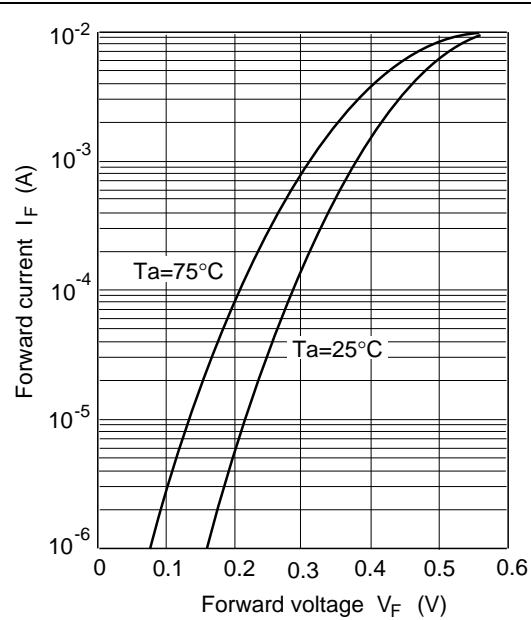


Fig.1 Forward current Vs. Forward voltage

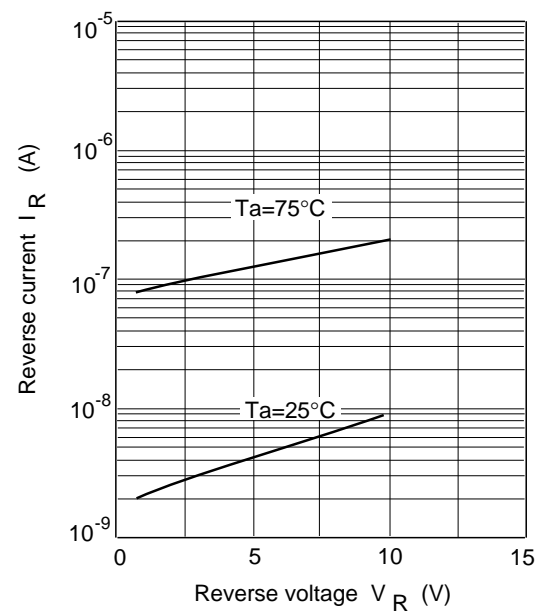


Fig.2 Reverse current Vs. Reverse voltage

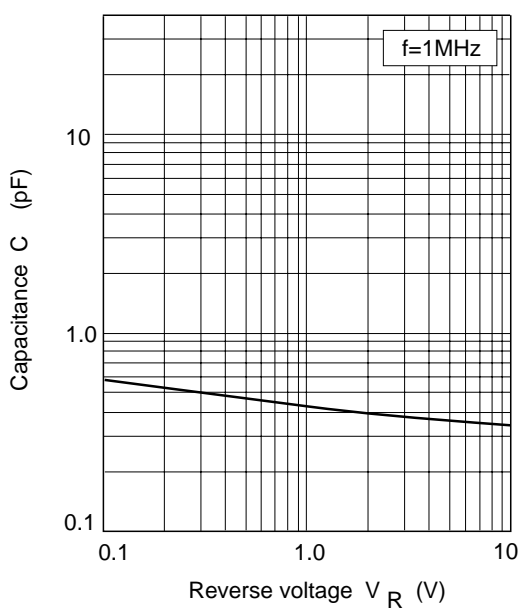
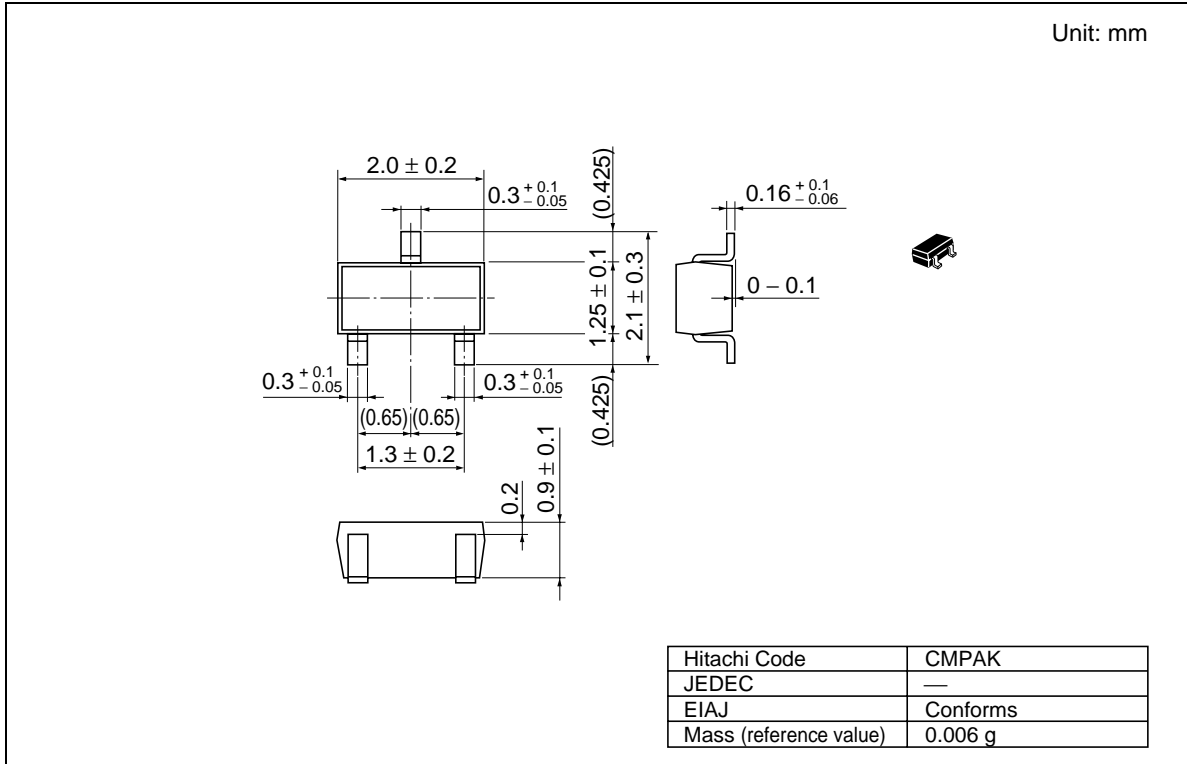


Fig.3 Capacitance Vs. Reverse voltage

# HSB88AS

## Package Dimensions



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**HITACHI****Hitachi, Ltd.**

Semiconductor & Integrated Circuits  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL      NorthAmerica      : <http://semiconductor.hitachi.com/>  
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**For further information write to:**

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe Ltd.  
Electronic Components Group  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 585200

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.  
Hitachi Tower  
16 Collyer Quay #20-00  
Singapore 049318  
Tel: <65>-538-6533/538-8577  
Fax : <65>-538-6933/538-3877  
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
(Taipei Branch Office)  
4/F, No. 167, Tun Hwa North Road  
Hung-Kuo Building  
Taipei (105), Taiwan  
Tel: <886>-(2)-2718-3666  
Fax : <886>-(2)-2718-8180  
Telex : 23222 HAS-TP  
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon  
Hong Kong  
Tel : <852>-(2)-735-9218  
Fax : <852>-(2)-730-0281  
URL : <http://semiconductor.hitachi.com.hk>